**Product data sheet** 

## 1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

## 2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

## 3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

## 4. Quick reference data

Table 1. Quick reference data

| Symbol             | Parameter                           | Conditions   | Min | Тур | Max | Unit |
|--------------------|-------------------------------------|--|-----|-----|-----|------|
| $V_{RRM}$          | repetitive peak reverse voltage     |  | -   | -   | 600 | V    |
| I <sub>F(AV)</sub> | average forward current             | $\delta$ = 0.5 ; T <sub>h</sub> ≤ 75 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3 | -   | -   | 8   | А    |
| I <sub>FRM</sub>   | repetitive peak forward current     | $\delta$ = 0.5 ; $t_p$ = 25 $\mu s;  T_h \le$ 75 °C; squarewave pulse              | -   | -   | 16  | Α    |
| I <sub>FSM</sub>   | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4                      | -   | -   | 91  | А    |
|                    |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4                     | -   | -   | 100 | А    |
| Static chara       | cteristics                          |  |     |     |     |      |
| V <sub>F</sub>     | forward voltage                     | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>                        | -   | -   | 3.4 | V    |
|                    |                                     | I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>                       | -   | 1.5 | 1.9 | V    |
|                    |                                     | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C                                      | -   | 1.4 | -   | V    |





## Hyperfast power diode

| Symbol          | Parameter               | Conditions  |  | Min | Тур | Max | Unit |
|-----------------|-------------------------|---|--|-----|-----|-----|------|
| Dynamic chara   | Dynamic characteristics |   |  |     |     |     |      |
| t <sub>rr</sub> | reverse recovery time   | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$  |  | -   | 12  | 18  | ns   |
|                 |                         | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$ |  | -   | 19  | -   | ns   |

# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description             | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|--------------------|----------------|
| 1   | K      | cathode                 | mb                 | K — A          |
| 2   | Α      | anode                   |                    | 001aaa020      |
| mb  | n.c.   | mounting base; isolated | TO-220F (SOD113)   |                |

# 6. Ordering information

Table 3. Ordering information

| Type number | Package |   |         |  |  |
|-------------|---------|---|---------|--|--|
|             | Name    | Description   | Version |  |  |
| BYC8X-600P  | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack" | SOD113  |  |  |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BYC8X-600P  | BYC8X-600P   |

Hyperfast power diode

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                           | Conditions   | Min | Max | Unit |
|--------------------|-------------------------------------|--|-----|-----|------|
| $V_{RRM}$          | repetitive peak reverse voltage     |  | -   | 600 | V    |
| $V_{RWM}$          | crest working reverse voltage       |  | -   | 600 | V    |
| V <sub>R</sub>     | reverse voltage                     | DC   | -   | 600 | V    |
| I <sub>F(AV)</sub> | average forward current             | $\delta$ = 0.5 ; T <sub>h</sub> ≤ 75 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3 | -   | 8   | А    |
| I <sub>FRM</sub>   | repetitive peak forward current     | $\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_h \le$ 75 °C; squarewave pulse             | -   | 16  | А    |
| I <sub>FSM</sub>   | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4                      | -   | 91  | А    |
|                    |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4                     | -   | 100 | А    |
| T <sub>stg</sub>   | storage temperature                 |  | -65 | 175 | °C   |
| Tj                 | junction temperature                |  | -   | 175 | °C   |

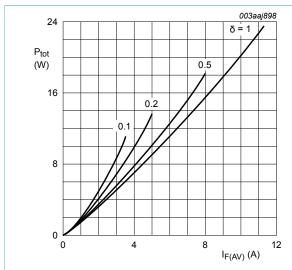


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_O &= 1.581 \text{ V; } R_S = 0.043 \text{ } \Omega \end{split}$$

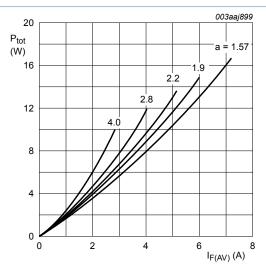


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor = 
$$I_{F(RMS)}/I_{F(AV)}$$
  
 $V_O = 1.581 \text{ V}; R_S = 0.043 \Omega$ 

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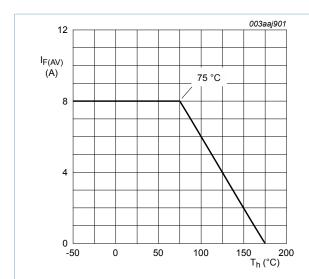


Fig. 3. Average forward current as a function of heatsink temperature; maximum values

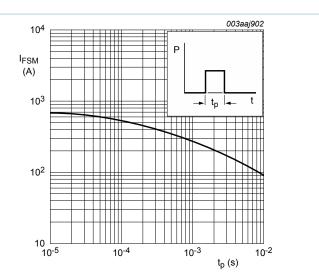


Fig. 4. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

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## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol               | Parameter  | Conditions                     | Min | Тур | Max | Unit |
|----------------------|--|--------------------------------|-----|-----|-----|------|
| R <sub>th(j-h)</sub> | thermal resistance   | without heatsink compound      | -   | -   | 7.2 | K/W  |
|                      | from junction to heatsink                                  | with heatsink compound; Fig. 5 | -   | -   | 5.5 | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance<br>from junction to<br>ambient free air |                                | -   | 60  | -   | K/W  |

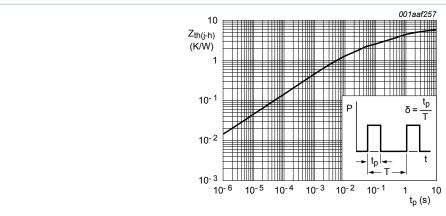


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse width

## 10. Isolation characteristics

Table 7. Isolation characteristics

| Symbol                 | Parameter             | Conditions   | Min | Тур | Max  | Unit |
|------------------------|-----------------------|--|-----|-----|------|------|
| V <sub>isol(RMS)</sub> | RMS isolation voltage | 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free | -   | -   | 2500 | V    |
| C <sub>isol</sub>      | isolation capacitance | from cathode to external heatsink  | -   | 10  | -    | pF   |

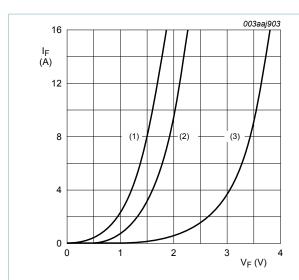
Hyperfast power diode

## 11. Characteristics

#### Table 8. Characteristics

| Symbol          | Parameter                     | Conditions  | Min | Тур | Max | Unit |
|-----------------|-------------------------------|---|-----|-----|-----|------|
| Static char     | acteristics                   |   |     |     |     |      |
| V <sub>F</sub>  | forward voltage               | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   | -   | -   | 3.4 | V    |
|                 |                               | I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>  | -   | 1.5 | 1.9 | V    |
|                 |                               | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C   | -   | 1.4 | -   | V    |
| I <sub>R</sub>  | reverse current               | V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C  | -   | -   | 20  | μA   |
|                 |                               | V <sub>R</sub> = 600 V; T <sub>j</sub> = 125 °C   | -   | -   | 200 | μA   |
| Dynamic cl      | haracteristics                |   | '   |     |     |      |
| Q <sub>r</sub>  | recovered charge              | $I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$ | -   | 17  | -   | nC   |
|                 |                               | $I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_j = 125 \text{ °C}; Fig. 7$                | -   | 90  | -   | nC   |
| t <sub>rr</sub> | reverse recovery time         | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$                  | -   | 12  | 18  | ns   |
|                 |                               | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$                 | -   | 19  | -   | ns   |
| I <sub>RM</sub> | peak reverse recovery current | $I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$                 | -   | -   | 2.2 | Α    |
|                 |                               | $I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$<br>$T_j = 125 \text{ °C}; Fig. 7$                | -   | -   | 6   | A    |

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(1)  $T_j = 125$  °C; typical values; (2)  $T_j = 125$  °C; maximum values; (3)  $T_j = 25$  °C; maximum values;  $V_O = 1.581$  V;  $R_S = 0.043$   $\Omega$ 

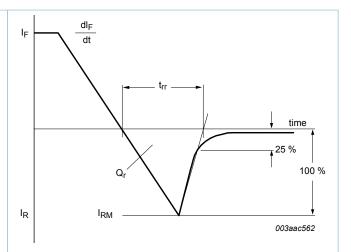
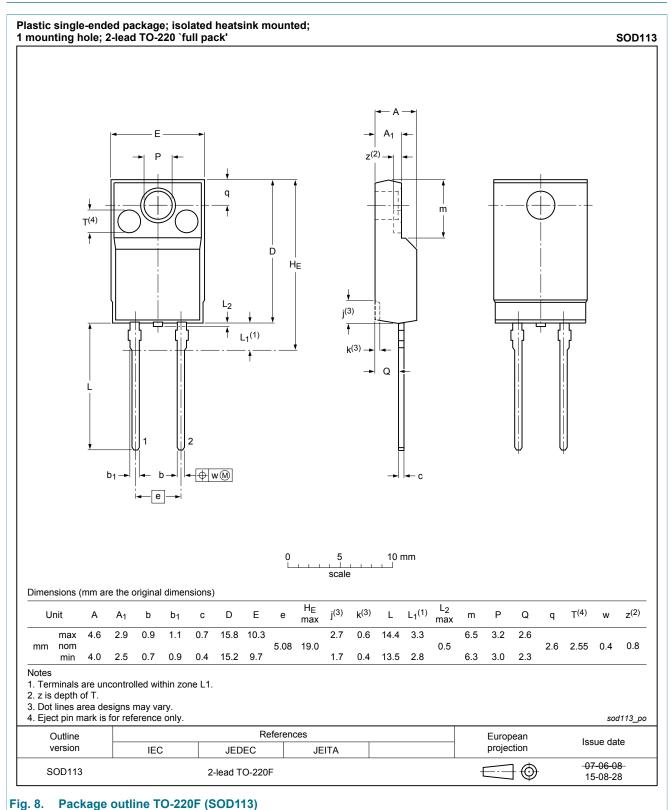


Fig. 7. Reverse recovery definitions; ramp recovery

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## 12. Package outline



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